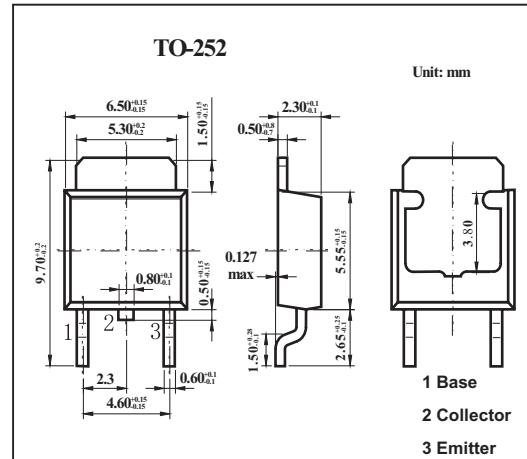


**Silicon PNP Epitaxial Planar Type****2SB932****■ Features**

- Low collector-emitter saturation voltage  $V_{CE(sat)}$ .
- Satisfactory linearity of forward current transfer ratio  $hFE$ .
- Large collector current  $I_C$ .

**■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$** 

Parameter	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	-130	V
Collector-emitter voltage	$V_{CEO}$	-80	V
Emitter-base voltage	$V_{EBO}$	-7	V
Collector current	$I_C$	-4	A
Peak collector current	$I_{CP}$	-8	A
Collector power dissipation	$P_C$	1.3	W
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

**■ Electrical Characteristics  $T_a = 25^\circ\text{C}$** 

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base cutoff current	$I_{CBO}$	$V_{CB} = -100 \text{ V}, I_E = 0$			-10	$\mu\text{A}$
Emitter-base cutoff current	$I_{EBO}$	$V_{EB} = -5 \text{ V}, I_C = 0$			-50	$\mu\text{A}$
Collector-emitter voltage	$V_{CEO}$	$I_C = -10\text{mA}, I_B = 0$	-80			V
Forward current transfer ratio	$hFE$	$V_{CE} = -2 \text{ V}, I_C = -1 \text{ A}$	90	260		V
		$V_{CE} = -2 \text{ V}, I_C = -0.1 \text{ A}$	45			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -3 \text{ A}, I_B = -0.15 \text{ A}$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -3 \text{ A}, I_B = -0.15 \text{ A}$			-1.5	V
Transition frequency	$f_T$	$V_{CE} = -10 \text{ V}, I_C = -0.5 \text{ A}, f = 10 \text{ MHz}$	30			MHz
Turn-on time	$t_{on}$	$I_C = -1 \text{ A}, I_{B1} = -0.1 \text{ A}, I_{B2} = 0.1 \text{ A},$		0.15		$\mu\text{s}$
Storage time	$t_{stg}$			0.8		$\mu\text{s}$
Fall time	$t_f$			0.15		$\mu\text{s}$

**■ hFE Classification**

Rank	Q	P
$hFE$	90~180	130~260